

2SC4115S TRANSISTOR (NPN)

FEATURES

Power dissipation

$$P_D: 0.3 \text{ W (Tamb=25°C)}$$

Collector current

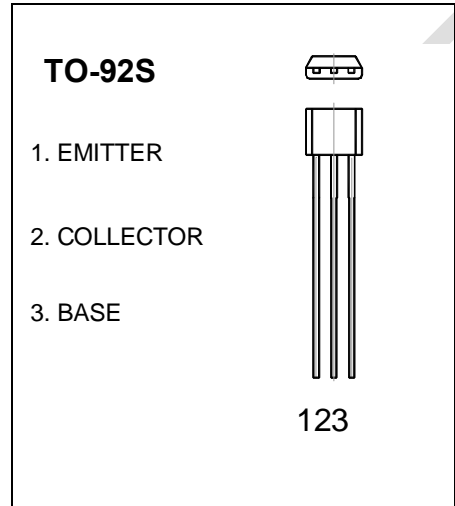
$$I_{CM}: 3 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO}: 40 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55°C \text{ to } +150°C$$



ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 50\mu A, I_E = 0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 1 \text{ mA}, I_B = 0$	20			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 50\mu A, I_C = 0$	6			V
Collector cut-off current	I_{CBO}	$V_{CB} = 30V, I_E = 0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5V, I_C = 0$			0.1	μA
DC current gain	h_{FE}	$V_{CE} = 2V, I_C = 0.1A$	120		560	
Collector-emitter saturation voltage*	V_{CEsat}	$I_C = 2A, I_B = 0.1A$			0.5	V
Transition frequency	f_T	$V_{CE} = 2V, I_C = 0.5A, F = 100MHz$	200			MHz

● Measured Using Pulse Current

CLASSIFICATION OF h_{FE}

Rank	Q	R	S
Range	120-270	180-390	270-560